

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L18	1	((@ad<"20050204" @riad<"20050204") and inalas with multiplication near layer and inp with etching near stopper near layer	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:30
L17	19	((@ad<"20050204" @riad<"20050204") and inalas near3 multiplication near layer and inp near3 etching stopper near layer and photodiode near avalanche	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:30
L16	174	((@ad<"20050204" @riad<"20050204") and inalas near3 multiplication near layer and inp near3 etching stopper near layer and photodiode	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:30
L15	181	((@ad<"20050204" @riad<"20050204") and inalas with multiplication near layer and inp with etching stopper near layer and photodiode	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:29
L14	4132	((@ad<"20050204" @riad<"20050204") and inalas with multiplication near layer and inp with etching stopper near layer	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:14
L13	5	((@ad<"20050204" @riad<"20050204") and field with strength same multiplication and (etch near stop or etching near stopper) and photodiode and avalanche	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:02
L12	5	((@ad<"20050204" @riad<"20050204") and field with strength same multiplication and (etch near stop or etching near stopper) and photodiode	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:02
L11	10	((@ad<"20050204" @riad<"20050204") and field with strength same multiplication and (etch near stop or etching near stopper)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:02
L10	9	((@ad<"20050204" @riad<"20050204") and field with strength same multiplication and etch near stop	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:01

L9	280	((@ad< "20050204" @riad< "20050204") and field with strength same multiplication	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:01
L8	0	((@ad< "20050204" @riad< "20050204") and field with strength same multiplication same (etching near stopper etch near stop)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:01
L7	0	((@ad< "20050204" @riad< "20050204") and field with strength with multiplication with (etching near stopper etch near stop)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:01
L6	5414408	((@ad< "20050204" @riad< "20050204") field with strength with multiplication with (etching near stopper etch near stop)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:01
L5	0	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and field with strength with multiplication with (etching near stopper etch near stop)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:00
L4	0	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and field with strength with multiplication with etch\$3 with stop\$3	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:00
L3	0	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and avalanche and field with strength with multiplication with etch\$3 with stop\$3	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 18:00
L2	21	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and multiplication near layer and avalanche and field near strength	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 17:54

L1	0	((@ad<"20050204" @riad<"20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and multiplication near layer and avalanche and field near strenght	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 17:54
S51	93	S47 and (@ad<"20050204" @riad<"20050204")	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:49
S50	1727	S48 and (@ad<"20050204" @riad<"20050204")	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:48
S49	6	S46 and (@ad<"20050204" @riad<"20050204")	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:48
S48	2048	257/184,186,190,438,e31.063, e31.064,e31.116.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:48
S47	118	S41 and S42 and S43 and S44	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:47
S46	16	S41 and S42 and S43 and S44 and S45	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:47
S45	23899	etch\$3 near stop\$3 near (layer or film)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:47
S44	479	multiplication near (layer or film)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:47
S43	87271	field near\$3 (layer or film)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:46
S42	239202	light near (absorb\$3 or receiv \$3)	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:46
S41	118324	apd or (avalanche near (photodiode or photodetector))	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:46
S40	1	((@ad<"20050204" @riad<"20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and multiplication near layer and avalanche and (etch etching) near stopper and field	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:15

S39	0	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and multiplication near layer and avalanche and (etch etching) near stopper and field near strength	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:14
S38	99	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and multiplication near layer and avalanche	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:14
S37	99	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and multiplication near layer	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:11
S36	0	((@ad< "20050204" @riad< "20050204") and semiconductor near substrate and (photo-detecting photodetector photodiode) and buffer and field and (etching near stopper near layer etch near stop near layer) and conductivity and field near strength and (lower less near than) and multiplication near layer	US-PGPUB; USPAT; USOCR	OR	ON	2009/03/16 11:10

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